

isc N-Channel MOSFET Transistor

40N05

• FEATURES

- Drain Current $I_D = 40A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 50V(\text{Min})$
- Static Drain-Source On-Resistance
: $R_{DS(on)} = 0.035 \Omega (\text{Max})$
- Fast Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

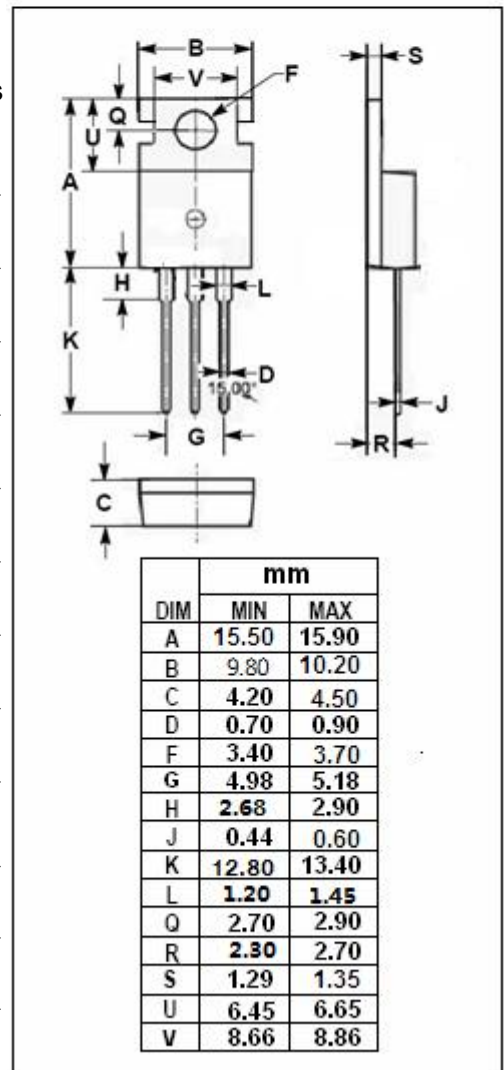
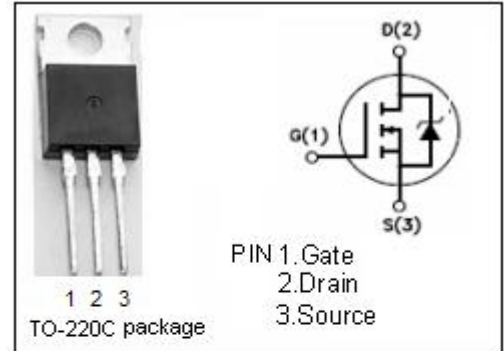
- Switching power supplies, converters, AC and DC motor controls

• ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|--|----------|------------|
| V_{DSS} | Drain-Source Voltage | 50 | V |
| V_{GS} | Gate-Source Voltage-Continuous | ± 30 | V |
| I_D | Drain Current-Continuous | 40 | A |
| I_{DM} | Drain Current-Single Plused | 100 | A |
| P_D | Total Dissipation @ $T_C = 25^\circ C$ | 120 | W |
| T_j | Max. Operating Junction Temperature | 150 | $^\circ C$ |
| T_{stg} | Storage Temperature | -55~150 | $^\circ C$ |

• THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|--------------|---|-------|--------------|
| $R_{th j-c}$ | Thermal Resistance, Junction to Case | 0.833 | $^\circ C/W$ |
| $R_{th j-a}$ | Thermal Resistance, Junction to Ambient | 62.5 | $^\circ C/W$ |



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• ELECTRICAL CHARACTERISTICS

T_c=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYPE | MAX | UNIT |
|----------------------|---------------------------------|---|-----|------|-------|------|
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0; I _D =250μA | 50 | | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} ; I _D =250μA | 2.0 | | 4.0 | V |
| V _{SD} | Diode Forward On-voltage | I _S = 40A; V _{GS} = 0 | | | 3.0 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D = 20A | | | 0.035 | Ω |
| I _{GSS} | Gate-Body Leakage Current | V _{GS} = ±20V; V _{DS} = 0 | | | ±500 | nA |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =50V; V _{GS} = 0 | | | 10 | μA |
| C _{iss} | Input Capacitance | V _{DS} =25V; | | | 5000 | pF |
| C _{rss} | Reverse Transfer capacitance | V _{GS} =0V; | | | 1000 | |
| C _{oss} | Output Capacitance | f _T =1MHz | | | 2500 | |
| t _r | Rise Time | V _{GS} =10V; | | | 330 | ns |
| t _{d(on)} | Turn-on Delay Time | I _D =20A; | | | 100 | |
| t _f | Fall Time | V _{DD} =25V; | | | 360 | |
| t _{d(off)} | Turn-off Delay Time | R _G =50 Ω | | | 330 | |

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